

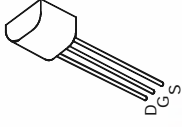
# N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 - SEPT 93

## FEATURES

- \* 200 Volt  $V_{DS}$
- \*  $R_{DS(on)} = 23\Omega$

# BS107P



E-Line  
TO92 Compatible

REFER TO BS107PT FOR GRAPHS

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	$V_{DS}$	200	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	$I_D$	0.12	A
Pulsed Drain Current	$I_{DM}$	2	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation at $T_{amb} = 25^{\circ}C$	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	$BV_{DSS}$	200	230		V	$I_D = 100\mu A, V_{GS} = 0V$
Gate Body Leakage	$I_{GSS}$			10	nA	$V_{GS} = 15V, V_{DS} = 0V$
Drain Cut-Off Current	$I_{DSS}$			30	nA	$V_{GS} = 0V, V_{DS} = 130V$
Drain Cut-Off Current	$I_{DSX}$			1	$\mu A$	$V_{GS} = 0.2V, V_{DS} = 70V$
Static Drain-Source on-State Resistance	$R_{DS(on)}$		15	23	$\Omega$	$V_{GS} = 2.6V, I_D = 25mA^*$
				30	$\Omega$	$V_{GS} = 5V, I_D = 100mA^*$

\* Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$

查询BS107P供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货